

|   | Type | L # | Hits   | Search Text  | DBs   | Time Stamp          | C<br>o<br>m<br>m<br>e<br>n<br>t<br>s | E<br>r<br>r<br>o<br>r<br>D<br>e<br>f<br>i<br>n<br>i<br>t<br>i<br>o<br>n | E<br>r<br>r<br>o<br>r<br>s |
|---|------|-----|--------|--|---|---------------------|--------------------------------------|---|----------------------------|
| 1 | BRS  | L1  | 4321   | (SiC or "silicon carbide") same etch\$3  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>12:43 |                                      |   | 0                          |
| 2 | BRS  | L8  | 15703  | CF4 or "carbon tetrafluoride" or<br>"CF.sub.4"   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>12:09 |                                      |   | 0                          |
| 3 | BRS  | L15 | 7504   | CHF3 or "carbon trifluoride" or<br>"trifluorocarbon" or "CHF.sub.3"                          | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>12:40 |                                      |   | 0                          |
| 4 | BRS  | L22 | 1193   | CH2F2 or "carbon difluoride" or<br>"difluoromethane" or "CH.sub.2 F.sub.2"                   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>12:39 |                                      |   | 0                          |
| 5 | BRS  | L29 | 13906  | CHF3 or "carbon trifluoride" or<br>"trifluorocarbon" or "CHF.sub.3" or<br>"trifluoromethane" | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>12:41 |                                      |   | 0                          |
| 6 | BRS  | L36 | 956347 | H2 or hydrogen or "H.sub.2"  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>12:42 |                                      |   | 0                          |
| 7 | BRS  | L43 | 502173 | NH3 or ammonia or "NH.sub.3"   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>12:42 |                                      |   | 0                          |
| 8 | BRS  | L57 | 62     | 1 same 29  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>12:43 |                                      |   | 0                          |

|    | Type | L #  | Hits | Search Text                           | DBs   | Time Stamp          | C<br>o<br>m<br>m<br>e<br>n<br>t<br>s | E<br>r<br>r<br>o<br>r<br>D<br>e<br>f<br>i<br>n<br>i<br>t<br>i<br>o<br>n | E<br>r<br>r<br>o<br>r<br>s |
|----|------|------|------|---------------------------------------|---|---------------------|--------------------------------------|---|----------------------------|
| 9  | BRS  | L64  | 174  | 1 same 8                              | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>12:44 |                                      |   | 0                          |
| 10 | BRS  | L71  | 0    | 50 same (36 or 43)                    | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>12:44 |                                      |   | 0                          |
| 11 | BRS  | L78  | 8    | 57 same (36 or 43)                    | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>12:44 |                                      |   | 0                          |
| 12 | BRS  | L92  | 4    | (low adj3 ("k" or dielectric)) and 78 | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>12:53 |                                      |   | 0                          |
| 13 | BRS  | L99  | 10   | (low adj3 ("k" or dielectric)) and 85 | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>12:48 |                                      |   | 0                          |
| 14 | BRS  | L106 | 186  | ("low k" or "low dielectric") same 1  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>14:15 |                                      |   | 0                          |
| 15 | BRS  | L113 | 143  | 106 and 438/\$.ccls.                  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>12:55 |                                      |   | 0                          |
| 16 | BRS  | L120 | 43   | 106 not 113                           | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>14:15 |                                      |   | 0                          |

|    | Type | L # | Hits | Search Text        | DBs   | Time Stamp          | C<br>o<br>m<br>m<br>e<br>n<br>t<br>s | E<br>r<br>r<br>o<br>r<br>D<br>e<br>f<br>i<br>n<br>i<br>t<br>i<br>o<br>n | E<br>r<br>r<br>o<br>r<br>s |
|----|------|-----|------|--------------------|---|---------------------|--------------------------------------|---|----------------------------|
| 17 | BRS  | L50 | 1    | 1 same 22          | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>14:22 |                                      |   | 0                          |
| 18 | BRS  | L85 | 40   | 64 same (36 or 43) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>14:27 |                                      |   | 0                          |

|     |     |  |   |                  |
|-----|-----|--|---|------------------|
| 92  | 4   | (low adj3 ("k" or dielectric)) and (((SiC or "silicon carbide") same etch\$3) same (CHF3 or "carbon trifluoride" or "trifluorocarbon" or "CHF.sub.3" or "trifluoromethane")) same ((H2 or hydrogen or "H.sub.2") or (NH3 or ammonia or "NH.sub.3"))) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 12:53 |
| 99  | 10  | (low adj3 ("k" or dielectric)) and (((SiC or "silicon carbide") same etch\$3) same (CF4 or "carbon tetrafluoride" or "CF.sub.4")) same ((H2 or hydrogen or "H.sub.2") or (NH3 or ammonia or "NH.sub.3")))  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 12:48 |
| 106 | 186 | ("low k" or "low dielectric") same ((SiC or "silicon carbide") same etch\$3)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 14:15 |
| 113 | 143 | ("low k" or "low dielectric") same ((SiC or "silicon carbide") same etch\$3)) and 438/\$.ccls.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 12:55 |
| 120 | 43  | ("low k" or "low dielectric") same ((SiC or "silicon carbide") same etch\$3)) not (("low k" or "low dielectric") same ((SiC or "silicon carbide") same etch\$3)) and 438/\$.ccls.)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 14:15 |
| 50  | 1   | ((SiC or "silicon carbide") same etch\$3) same (CH2F2 or "carbon difluoride" or "difluoromethane" or "CH.sub.2 F.sub.2")   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 14:22 |

| L Number | Hits   | Search Text   | DB  | Time stamp       |
|----------|--------|---|---|------------------|
| 1        | 4321   | (SiC or "silicon carbide") same etch\$3   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 12:43 |
| 8        | 15703  | CF4 or "carbon tetrafluoride" or "CF.sub.4"   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 12:09 |
| 15       | 7504   | CHF3 or "carbon trifluoride" or "trifluorocarbon" or "CHF.sub.3"  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 12:40 |
| 22       | 1193   | CH2F2 or "carbon difluoride" or "difluoromethane" or "CH.sub.2 F.sub.2"   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 12:39 |
| 29       | 13906  | CHF3 or "carbon trifluoride" or "trifluorocarbon" or "CHF.sub.3" or "trifluoromethane"  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 12:41 |
| 36       | 956347 | H2 or hydrogen or "H.sub.2"   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 12:42 |
| 43       | 502173 | NH3 or ammonia or "NH.sub.3"  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 12:42 |
| 57       | 62     | ((SiC or "silicon carbide") same etch\$3) same (CHF3 or "carbon trifluoride" or "trifluorocarbon" or "CHF.sub.3" or "trifluoromethane")   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 12:43 |
| 64       | 174    | ((SiC or "silicon carbide") same etch\$3) same (CF4 or "carbon tetrafluoride" or "CF.sub.4")  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 12:44 |
| 71       | 0      | ((SiC or "silicon carbide") same etch\$3) same (CH2F2 or "carbon difluoride" or "difluoromethane" or "CH.sub.2 F.sub.2")) same ((H2 or hydrogen or "H.sub.2") or (NH3 or ammonia or "NH.sub.3"))                | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 12:44 |
| 78       | 8      | ((SiC or "silicon carbide") same etch\$3) same (CHF3 or "carbon trifluoride" or "trifluorocarbon" or "CHF.sub.3" or "trifluoromethane")) same ((H2 or hydrogen or "H.sub.2") or (NH3 or ammonia or "NH.sub.3")) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 12:44 |
| 85       | 40     | ((SiC or "silicon carbide") same etch\$3) same (CF4 or "carbon tetrafluoride" or "CF.sub.4")) same ((H2 or hydrogen or "H.sub.2") or (NH3 or ammonia or "NH.sub.3"))  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08 12:45 |

|   | Type | L # | Hits             | Search Text                             | D<br>B<br>s   | Ti<br>me<br>St<br>a<br>m<br>p                               | C<br>o<br>m<br>m<br>e<br>n<br>t<br>s | E<br>r<br>r<br>o<br>r<br>D<br>e<br>f<br>i<br>n<br>i<br>t<br>i<br>o<br>n | E<br>r<br>r<br>o<br>r<br>s |
|---|------|-----|------------------|---|---|---|--------------------------------------|---|----------------------------|
| 1 | BRS  | L1  | 4<br>3<br>2<br>1 | (SiC or "silicon carbide") same etch\$3 | U<br>S<br>P<br>A<br>T;<br>U<br>S<br>P<br>P<br>G<br>P<br>U<br>B;<br>E<br>E<br>P<br>O;<br>J<br>P<br>O;<br>D<br>E<br>R<br>W<br>E<br>N<br>T;<br>I<br>B<br>M<br>-<br>T<br>D<br>B | 2<br>0<br>0<br>3/<br>0<br>3/<br>0<br>8<br>1<br>2:<br>4<br>3 |                                      |   | 0                          |

|   | Type | L # | Hits                  | Search Text                                 | D<br>B<br>s   | Ti<br>me<br>St<br>am<br>p                                   | C<br>o<br>m<br>m<br>e<br>n<br>t<br>s | E<br>r<br>r<br>o<br>r<br>s |
|---|------|-----|-----------------------|---|---|---|--------------------------------------|----------------------------|
| 2 | BRS  | L8  | 1<br>5<br>7<br>0<br>3 | CF4 or "carbon tetrafluoride" or "CF.sub.4" | U<br>S<br>P<br>A<br>T;<br>U<br>S<br>P<br>P<br>G<br>P<br>U<br>B;<br>E<br>E<br>P<br>O;<br>J<br>P<br>O;<br>D<br>E<br>R<br>W<br>E<br>N<br>T;<br>I<br>B<br>M<br>-<br>T<br>D<br>B | 2<br>0<br>0<br>3/<br>0<br>3/<br>0<br>8<br>1<br>2:<br>0<br>9 |                                      | 0                          |

|   | Type | L # | Hits | Search Text   | DBs   | Time Stamp          | C<br>o<br>m<br>m<br>e<br>n<br>t<br>s | E<br>r<br>r<br>o<br>r<br>m<br>e<br>s<br>s<br>a<br>g<br>e<br>s | E<br>r<br>r<br>o<br>r<br>m<br>e<br>s<br>s<br>a<br>g<br>e<br>s |
|---|------|-----|------|---|---|---------------------|--------------------------------------|---|---|
| 4 | BRS  | L22 | 200  | (SiC or "silicon carbide") same (etch\$3)<br>same (CF4 or "carbon tetrafluoride" or<br>"CF.sub.4" or trifluoromethane or CHF3 or<br>"CHF.sub.3" or difluoromethane or CH2F2<br>or "CH.sub.2 F.sub.2") | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/03/08<br>11:57 |                                      |   | 0   |